



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	$8\Omega @ V_{GS} = 5V$	SOT363	170mA
607	6Ω @ V <sub>GS</sub> = 10V	501363	200mA

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relavs
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories. Transistors. etc.

#### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

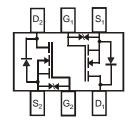
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208@3)
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)





Top View



Top View Internal Schematic

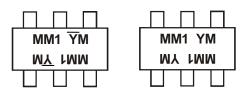
#### Ordering Information (Note 4)

Ī	Part Number	Case	Packaging
	DMN65D8LDW-7	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

# **Marking Information**



MM1= Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or Y = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	U	V	W	Х	Υ	Z	Α	В	С	D	E	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# 

	Characteristic	Symbol	Value	Units		
Drain-Source Voltage				V <sub>DSS</sub>	60	V
Gate-Source Voltage				V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	180 140	mA
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	150 120	mA
Continuous Drain Current (Note 6)	V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	200 160	mA
Continuous Drain Current (Note 6)	V <sub>GS</sub> = 5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	170 140	mA
Pulsed Drain Current (10µs pulse, du	ty cycle = 1%)			I <sub>DM</sub>	800	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	435	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	400	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	330	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>0</sub> JC	139	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

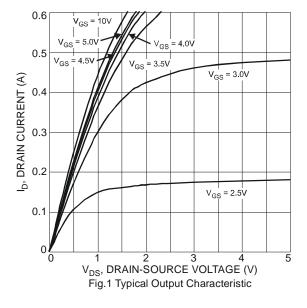
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

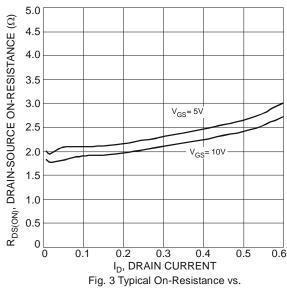
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}\text{C}$ $T_J = +125^{\circ}\text{C}$ (Note 8)	I <sub>DSS</sub>	_	_	1.0 5.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_		±5.0	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	•				•		
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$	
Static Drain-Source On-Resistance	0	_	_	8	Ω	$V_{GS} = 5.0V, I_D = 0.115A$	
Static Drain-Source On-Nesistance	R <sub>DS</sub> (ON)	_	_	6	Ω	$V_{GS} = 10.0V, I_D = 0.115A$	
Forward Transconductance	<b>g</b> FS	80			mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		22.0	_		V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss		3.2		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.0	_			
Gate Resistance	$R_{G}$	_	79.9	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge V <sub>GS</sub> = 10V	$Q_g$	_	0.87	_			
Total Gate Charge V <sub>GS</sub> = 4.5V	Qg	_	0.43	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$	
Gate-Source Charge	$Q_{gs}$	_	0.11	_	110	$I_D = 150 \text{mA}$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.11	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	3.3	_			
Turn-On Rise Time	t <sub>r</sub>	_	3.2	_	nS	$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	12.0	_	113	$R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	6.3	_			

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

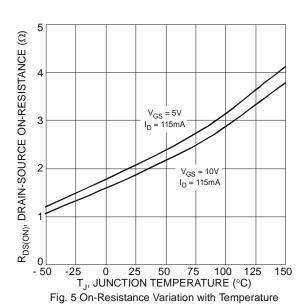
Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

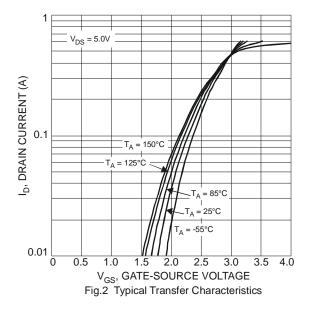


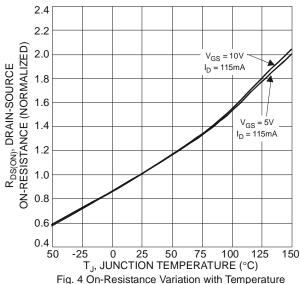




Drain Current and Temperature







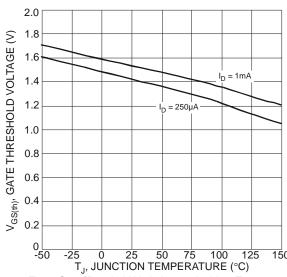
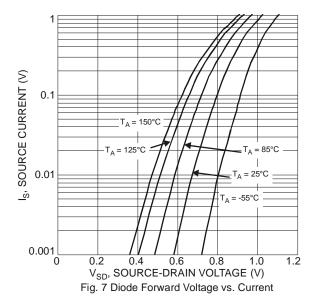


Fig. 6 Gate Threshold Variation vs. Ambient Temperature





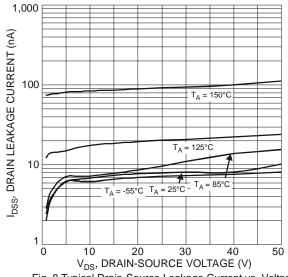
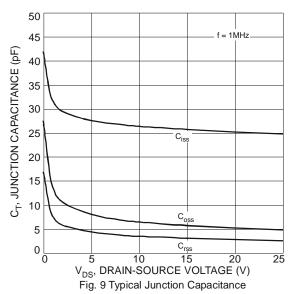
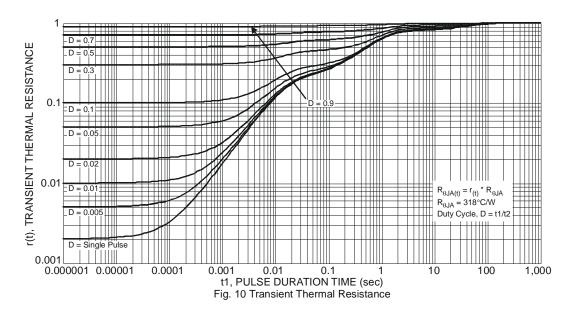


Fig. 8 Typical Drain-Source Leakage Current vs. Voltage

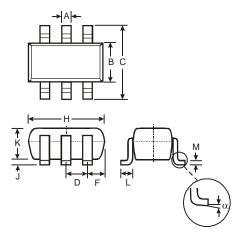






# **Package Outline Dimensions**

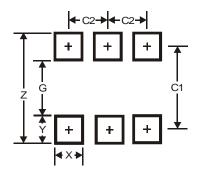
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT363					
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D		0.65 Ty	'p		
F	0.40	0.45	0.425		
Н	1.80	2.20	2.15		
J	0	0.10	0.05		
K	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
All	All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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